

### **General Description**

The WSD6060DN56 is the highest performance trench N-Ch MOSFET with extreme high cell density,which provide excellent  $R_{DSON}$  and gate charge for most of the synchronous buck converter applications .

The WSD6060DN56 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

#### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

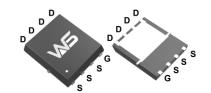
### **Product Summery**

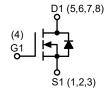
BV <sub>DSS</sub>	R <sub>DSON</sub>	I <sub>D</sub>
60V	7.5mΩ	65A

# **Applications**

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Fast switching
- Load Switch

### **DFN5X6-8L Pin Configuration**





# **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Unit				
Commor	Common Ratings						
V <sub>DSS</sub>	Drain-Source Voltage	60	V				
V <sub>GSS</sub>	Gate-Source Voltage		±20	V			
TJ	Maximum Junction Temperature		150	°C			
T <sub>STG</sub>	Storage Temperature Range		-55 to 150	°C			
Is	Diode Continuous Forward Current	T <sub>c</sub> =25°C	30	Α			
	Continuous Drain Current	T <sub>c</sub> =25°C	65				
I <sub>D</sub>		T <sub>c</sub> =70°C	42	Α			
I <sub>DM</sub> <sup>b</sup>	Pulse Drain Current Tested	T <sub>c</sub> =25°C	250	Α			
P <sub>D</sub>	Maximum Power Dissipation	T <sub>c</sub> =25°C	62.5	100			
		T <sub>C</sub> =70°C	38	W			
R <sub>θJL</sub>	Thermal Resistance-Junction to Lead	Steady State	2.1	°C/W			
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	t≤10s	45	°C/W			
		Steady State <sup>b</sup>	50				
l <sub>AS</sub> d	Avalanche Current, Single pulse	L=0.5mH	18	Α			
E <sub>AS</sub> d	Avalanche Energy, Single pulse	L=0.5mH	81	mJ			

Note a: Max. continuous current is limited by bonding wire.

Note b: Pulse width limited by max. junction temperature.

Note c : Surface mounted on 1in<sup>2</sup> pad area, steady state t = 999s.

Note d: UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T<sub>i</sub>=25°C).



# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	
Static Cha	Static Characteristics						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS}$ =0V, $I_{DS}$ =250 $\mu$ A	60	-	-	V	
1	Zero Gate Voltage Drain Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V	-	-	1	^	
I <sub>DSS</sub>		T <sub>J</sub> =85°C	-	-	30	- μΑ	
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{DS}=250\mu A$	1.2	1.5	2.5	V	
I <sub>GSS</sub>	Gate Leakage Current	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA	
D 3	Danie Course On state Besietenes	V <sub>GS</sub> =10V, I <sub>DS</sub> =20A	-	7.5	10	m Ω	
R <sub>DS(ON)</sub> <sup>3</sup>	Drain-Source On-state Resistance	V <sub>GS</sub> =4.5V, I <sub>DS</sub> =15 A	-	10	15		
Diode Cha	Diode Characteristics						
V <sub>SD</sub>	Diode Forward Voltage	I <sub>SD</sub> =1A, V <sub>GS</sub> =0V	-	0.75	1.2	V	
t <sub>rr</sub>	Reverse Recovery Time	1 -20A dl /dt-100A/.a	-	42	-	ns	
Q <sub>rr</sub>	Reverse Recovery Charge	$I_{SD}$ =20A, $dI_{SD}/dt$ =100A/ $\mu$ s	-	36	-	nC	
Dynamic (	Characteristics <sup>3,4</sup>	<u> </u>	•	•	'		
$R_G$	Gate Resistance	V <sub>GS</sub> =0V,V <sub>DS</sub> =0V,F=1MHz	-	1.5	-	Ω	
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V,	-	1340	-	pF	
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =30V,	-	270	-		
C <sub>rss</sub>	Reverse Transfer Capacitance	F=1.0MHz Ω	-	40	-		
t <sub>d(ON)</sub>	Turn-on Delay Time		-	6	-		
t <sub>r</sub>	Turn-on Rise Time	VDD=30V, lps=1A,	-	15	-	ne	
t <sub>d(OFF)</sub>	Turn-off Delay Time	V <sub>GEN</sub> =10V,	-	30	-	- ns -	
t <sub>f</sub>	Turn-off Fall Time	R <sub>G</sub> =6Ω.	-	33	-		
Gate Char	ge Characteristics 3,4						
Qg	Total Gate Charge	V <sub>DS</sub> =30V, V <sub>GS</sub> =4.5V, I <sub>DS</sub> =20A	-	13	-		
$Q_g$	Total Gate Charge		-	27	-		
Q <sub>gth</sub>	Threshold Gate Charge	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V,	-	4.1	-	nC	
Q <sub>gs</sub>	Gate-Source Charge	I <sub>DS</sub> =20A	-	5	-		
$Q_{gd}$	Gate-Drain Charge		-	4.2	-		

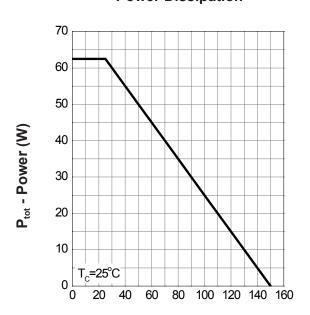
#### Note

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2.  $V_{DD}=48V, V_{GS}=10V, L=0.1 mH, I_{AS}=20A., R_{G}=25\Omega$  Starting T<sub>J</sub>=25
- 3. The data tested by pulsed , pulse width<=300us , duty cycle<=2%.
- 4. Essentially independent of operating temperature.



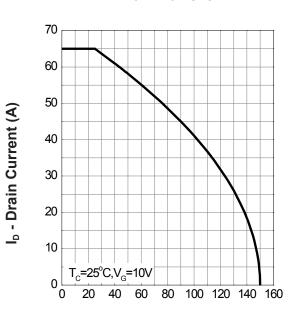
# **Typical Operating Characteristics**

# **Power Dissipation**



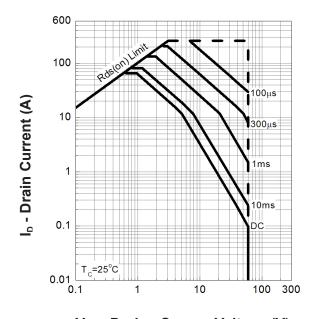
T<sub>j</sub> - Junction Temperature (°C)

#### **Drain Current**



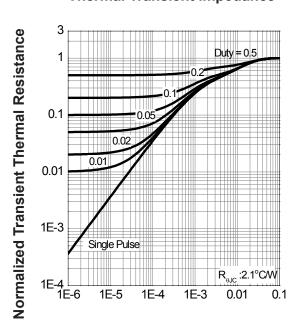
T<sub>j</sub> - Junction Temperature (°C)

### **Safe Operation Area**



V<sub>DS</sub> - Drain - Source Voltage (V)

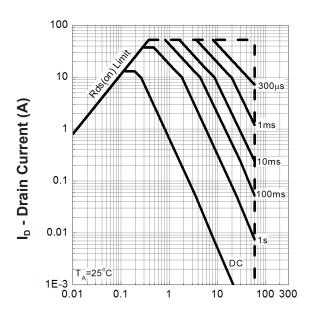
### **Thermal Transient Impedance**



**Square Wave Pulse Duration (sec)** 

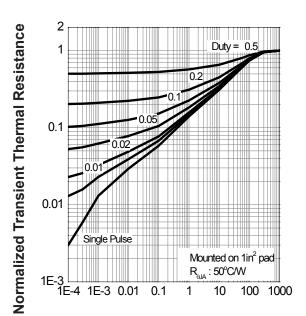


# **Safe Operation Area**



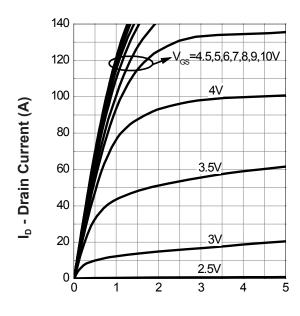
V<sub>DS</sub> - Drain - Source Voltage (V)

# **Thermal Transient Impedance**



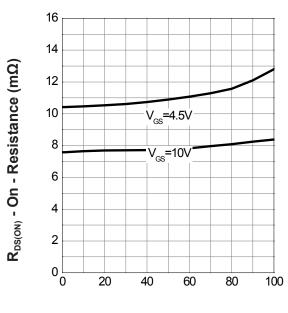
**Square Wave Pulse Duration (sec)** 

### **Output Characteristics**



V<sub>DS</sub> - Drain - Source Voltage (V)

#### **Drain-Source On Resistance**

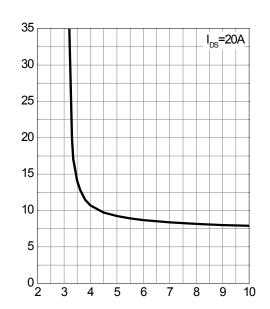


I<sub>D</sub> - Drain Current (A)



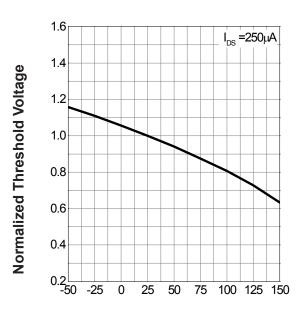
R<sub>DS(ON)</sub> - On - Resistance (mΩ)

### **Gate-Source On Resistance**



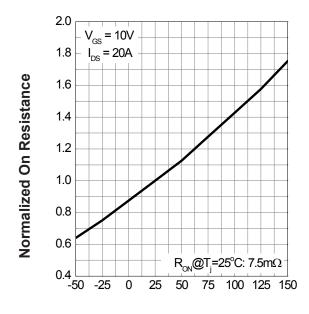
V<sub>GS</sub> - Gate - Source Voltage (V)

# **Gate Threshold Voltage**



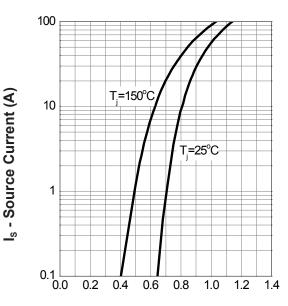
T<sub>i</sub> - Junction Temperature (°C)

# **Drain-Source On Resistance**



T<sub>j</sub> - Junction Temperature (°C)

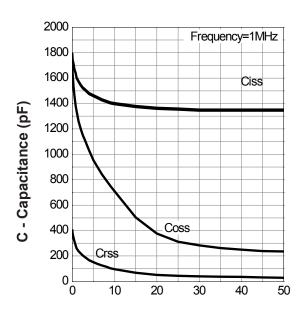
#### Source-Drain Diode Forward



V<sub>SD</sub> - Source - Drain Voltage (V)

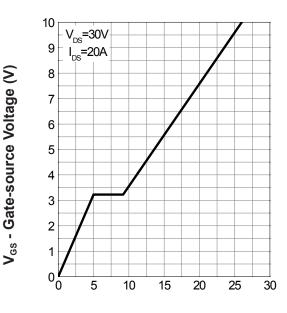






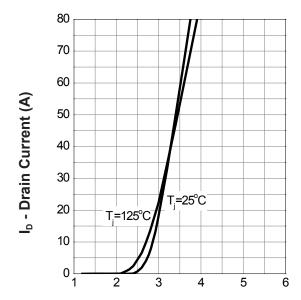
V<sub>DS</sub> - Drain-Source Voltage (V)

# **Gate Charge**



**Q**<sub>G</sub> - Gate Charge (nC)

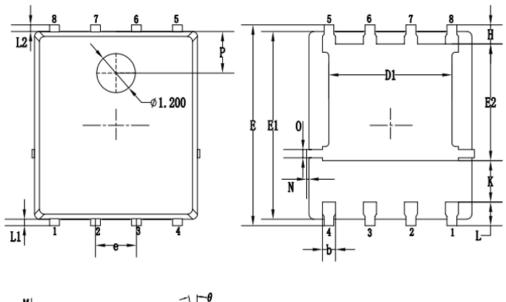
### **Transfer Characteristics**

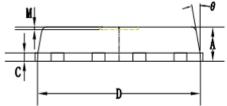


V<sub>GS</sub> - Gate-Source Voltage (V)



# **Packaging information**





SYMBOLS	MILLIMETERS					
	MIN.	NOM.	MAX.			
А	0.90	1.05	1.20			
b	0.35	0.40	0.50			
С	0.20	0.25	0.35			
D	4.90	5.05	5.20			
D1	3.72	3.82	3.92			
E	6.00	6.15	6.30			
E1	5.60	5.75	5.90			
E2	3.47	3.57	3.67			
е		1.27 BSC.				
Н	0.48	0.58	0.68			
К	1.17	1.27	1.37			
L	0.64	0.74	0.84			
L1/L2		0.20 REF.				
θ	8°	10°	12°			
М		0.08 REF.				
N	0	-	0.15			
0		0.25 REF.				
Р		1.28 REF.				



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